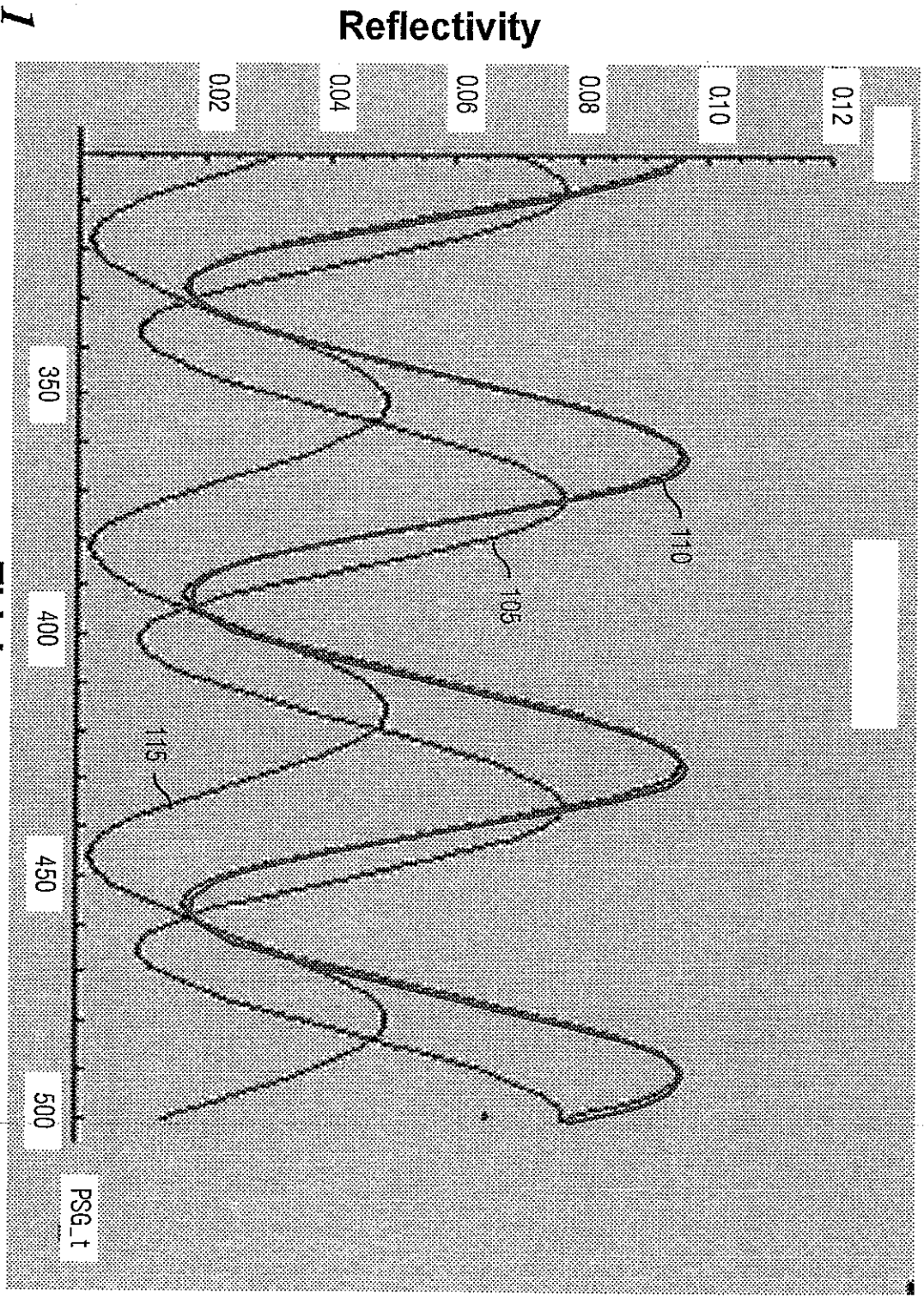
Fig. 1


Reflectivity
0.12
0.10
0.08
0.06
0.04
0.02
110
105
115
350
400
450
500
PSG_t
Thickness

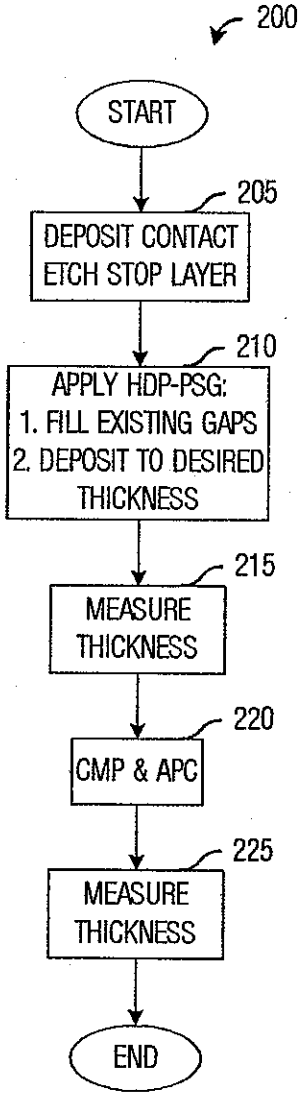


Fig. 2
(Prior Art)

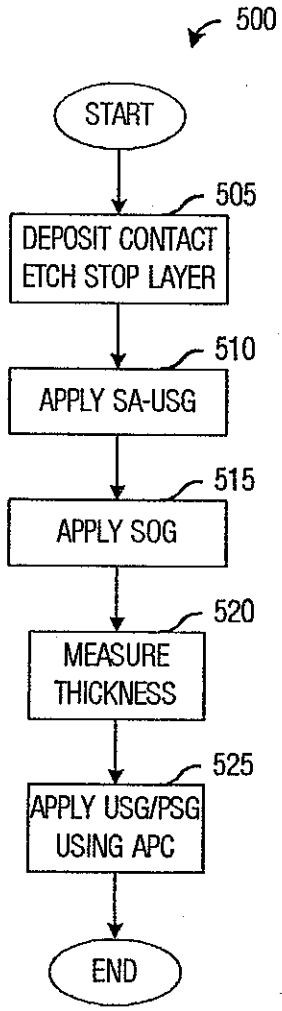


Fig. 5

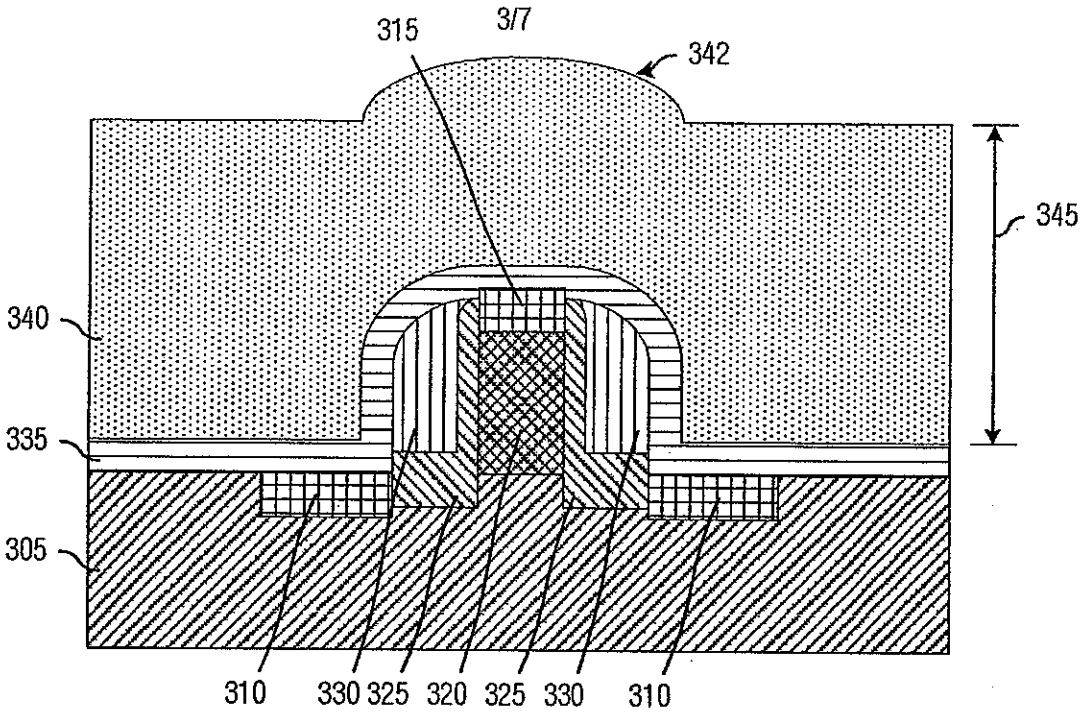


Fig. 3a
(Prior Art)

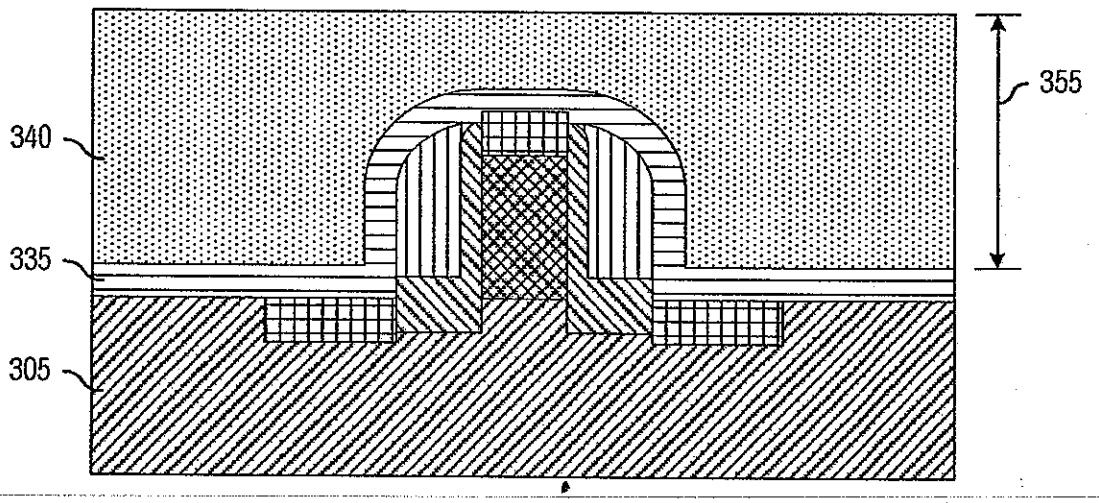


Fig. 3b
(Prior Art)

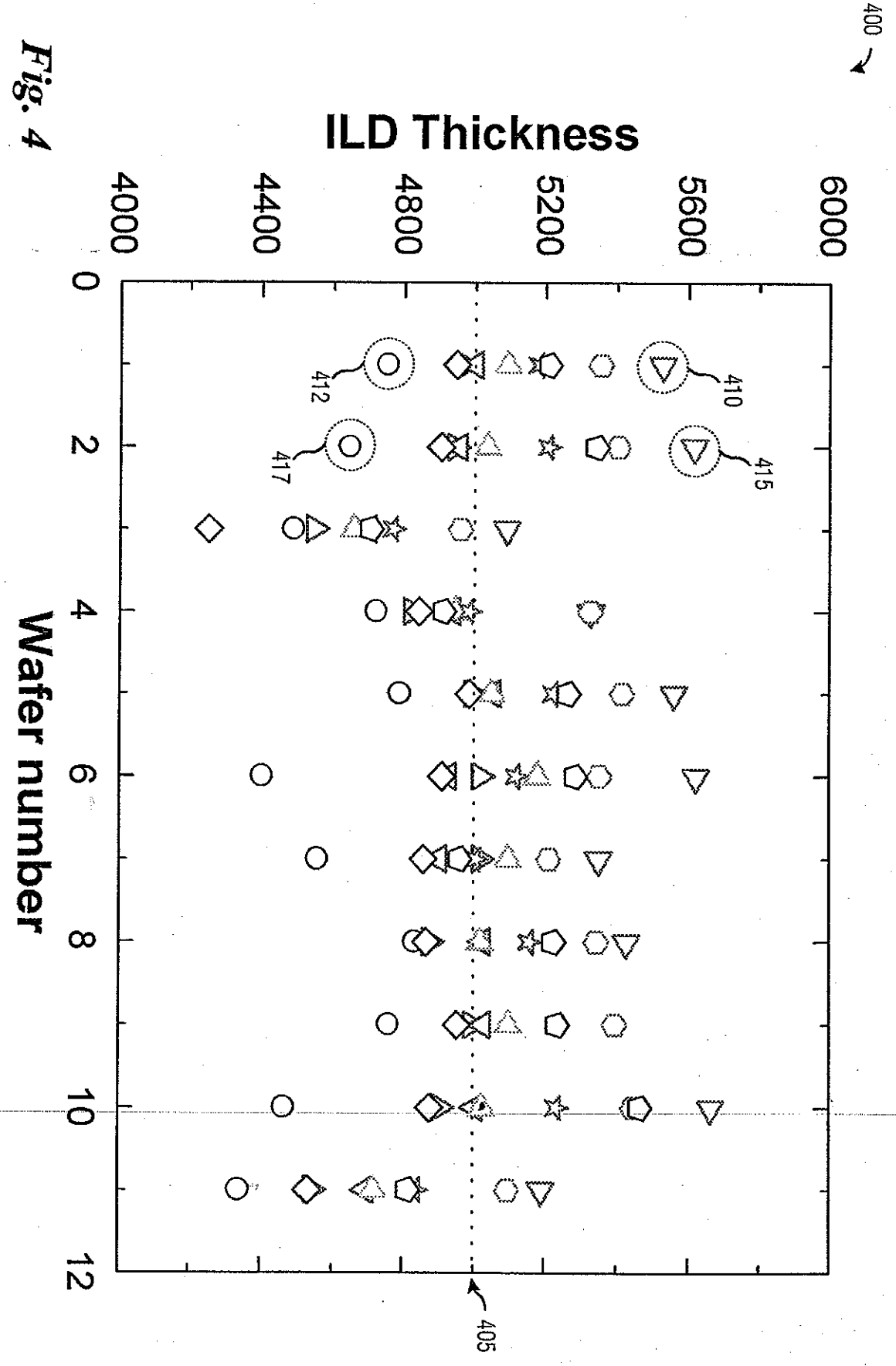

400
ILD Thickness
4000
4400
4800
5200
5600
6000
0
2
4
6
8
10
12
Wafer number
410
412
415
417
405

Fig. 4

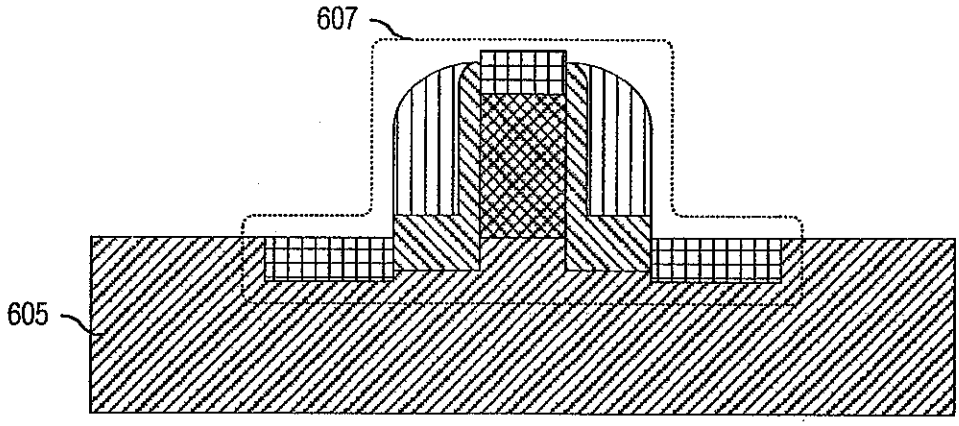


Fig. 6a

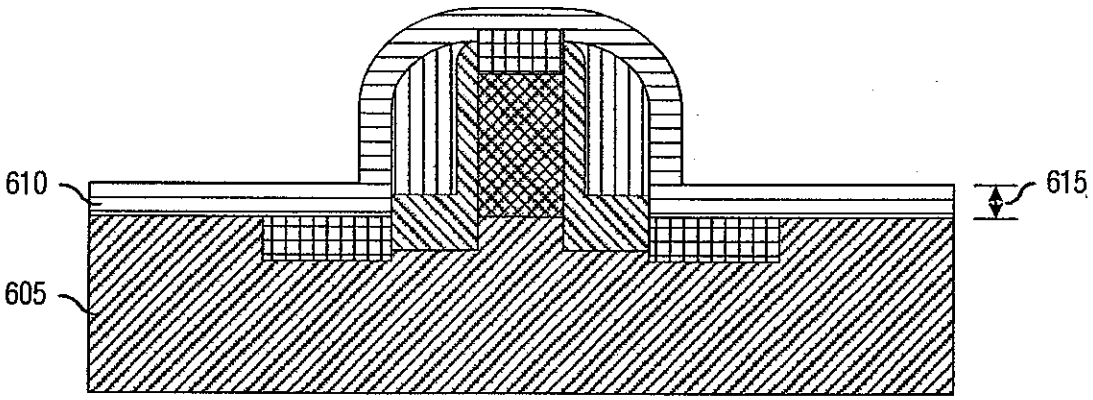


Fig. 6b

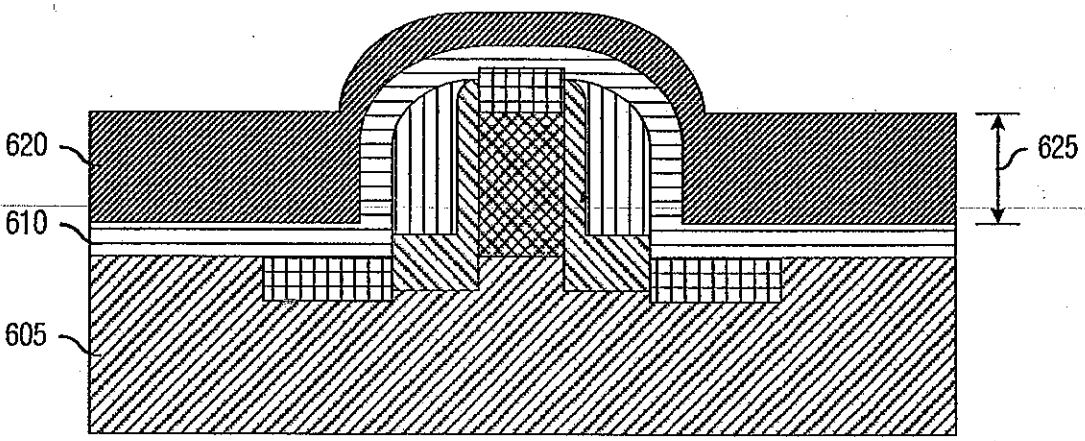


Fig. 6c

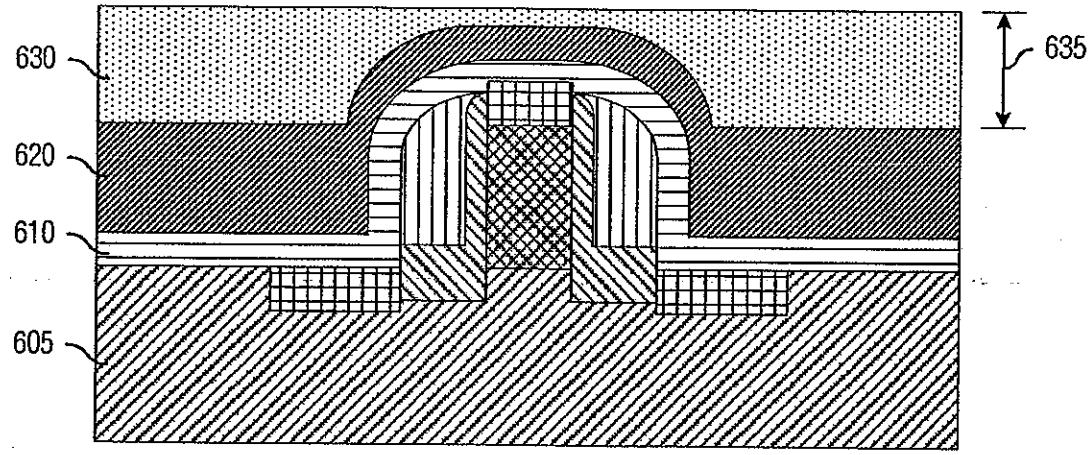


Fig. 6d

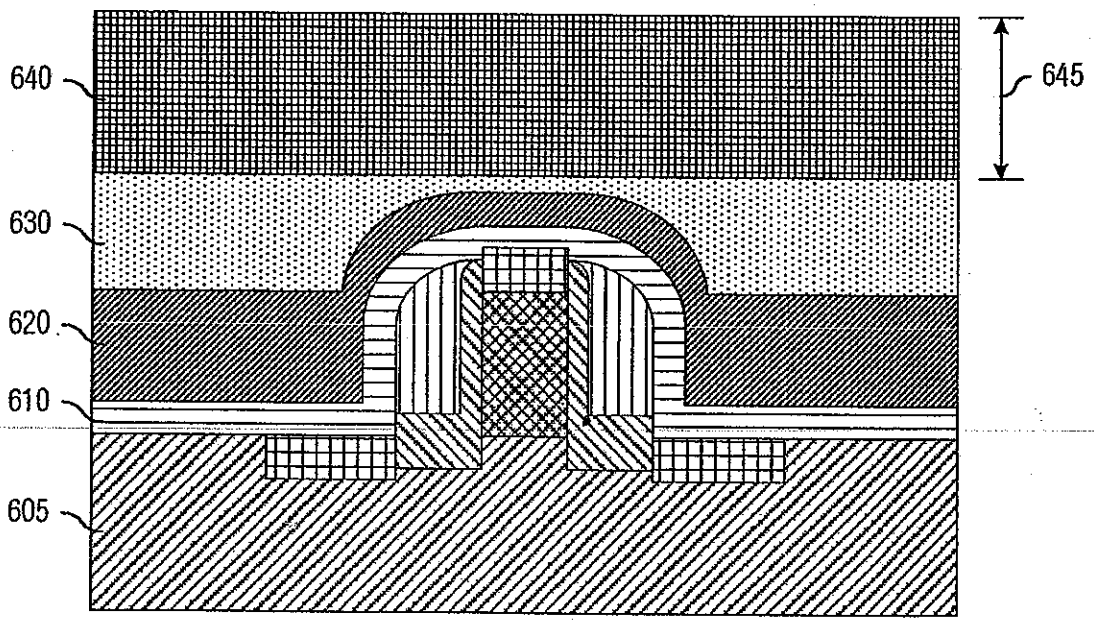


Fig. 6e

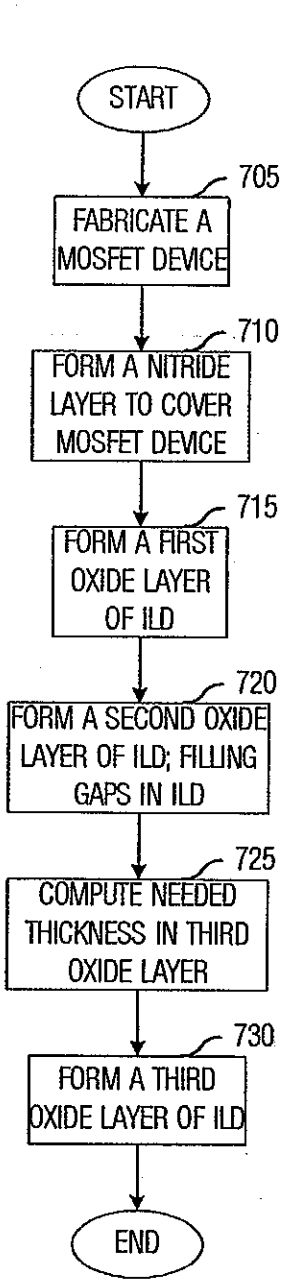

700
START
705
FABRICATE A MOSFET DEVICE
710
FORM A NITRIDE LAYER TO COVER MOSFET DEVICE
715
FORM A FIRST OXIDE LAYER OF ILD
720
FORM A SECOND OXIDE LAYER OF ILD; FILLING GAPS IN ILD
725
COMPUTE NEEDED THICKNESS IN THIRD OXIDE LAYER
730
FORM A THIRD OXIDE LAYER OF ILD
END

Fig. 7